

SWITCHMODE SERIES NPN POWER TRANSISTORS

... designed for use in high-voltage, high-speed, power switching in inductive circuit, they are particularly suited for 115 and 220 V switchmode applications such as switching regulator's, converter.

FEATURES:

*Collector-Emitter Sustaining Voltage-

$$V_{CEO(sus)} = 400 \text{ V (Min)}$$

* Collector-Emitter Saturation Voltage -

$$V_{CE(sat)} = 1.5 \text{ V (Max.) @ } I_C = 5.0 \text{ A, } I_B = 0.5 \text{ A}$$

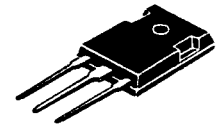
* Switching Time - $t_f = 1.0 \text{ us (Max.) @ } I_C = 5.0 \text{ A}$

NPN
2SC3306

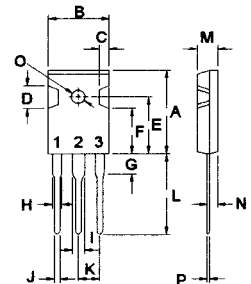
10 AMPERE
SILICON POWER
TRANSISTORS
400 VOLTS
100 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	2SC3306	Unit
Collector-Emitter Voltage	V_{CEO}	400	V
Collector-Base Voltage	V_{CBO}	500	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	10	A
- Peak	I_{CM}	15	
Base current	I_B	5.0	A
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	100 0.8	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$



TO-247(3P)



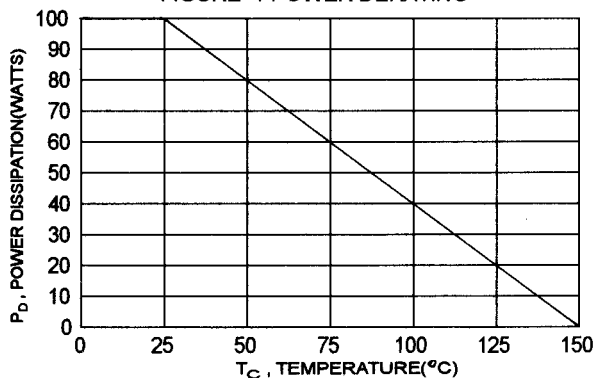
PIN 1.BASE
2.COLLECTOR
3.EMITTER

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	1.25	$^\circ\text{C/W}$

DIM	MILLIMETERS	
	MIN	MAX
A	20.63	22.38
B	15.38	16.20
C	1.90	2.70
D	5.10	6.10
E	14.81	15.22
F	11.72	12.84
G	4.20	4.50
H	1.82	2.46
I	2.92	3.23
J	0.89	1.53
K	5.26	5.66
L	18.50	21.50
M	4.68	5.36
N	2.40	2.80
O	3.25	3.65
P	0.55	0.70

FIGURE -1 POWER DERATING



ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Base Breakdown Voltage ($I_C = 1.0 \text{ mA}$, $I_E = 0$)	$V_{(BR)CBO}$	500		V
Collector-Emitter Breakdown Voltage ($I_C = 10 \text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	400		V
Emitter-Base Breakdown Voltage ($I_E = 1.0 \text{ mA}$, $I_C = 0$)	$V_{(BR)EBO}$	7.0		V
Collector Cutoff Current ($V_{CB} = 400 \text{ V}$, $I_E = 0$)	I_{CBO}		100	μA
Emitter Cutoff Current ($V_{EB} = 7.0 \text{ V}$, $I_C = 0$)	I_{EBO}		1.0	mA

ON CHARACTERISTICS (1)

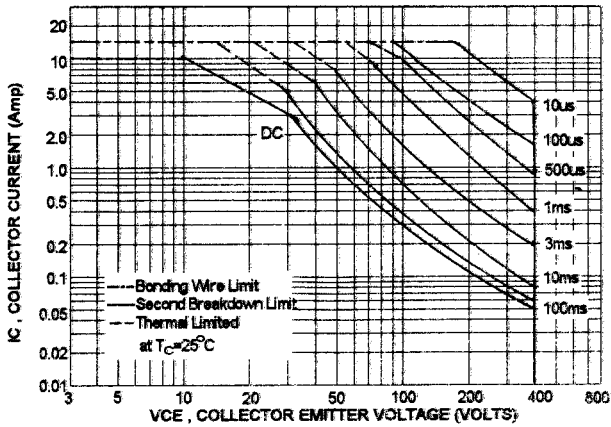
DC Current Gain ($I_C = 5.0 \text{ A}$, $V_{CE} = 5.0 \text{ V}$)	hFE	10		
Collector-Emitter Saturation Voltage ($I_C = 5.0 \text{ A}$, $I_B = 500 \text{ mA}$)	$V_{CE(sat)}$		1.5	V
Base-Emitter Saturation Voltage ($I_C = 5.0 \text{ A}$, $I_B = 500 \text{ mA}$)	$V_{BE(sat)}$		2.0	V

SWITCHING CHARACTERISTICS

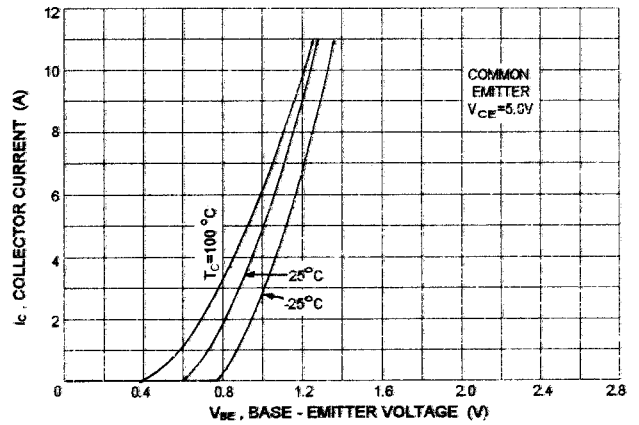
Rise Time	$V_{CC} = 200 \text{ V}$, $I_C = 5.0 \text{ A}$ $I_{B1} = -I_{B2} = 500 \text{ mA}$ $R_L = 40 \text{ ohm}$	t_r	1.0	μs
Storage Time		t_s	2.5	μs
Fall Time		t_f	1.0	μs

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

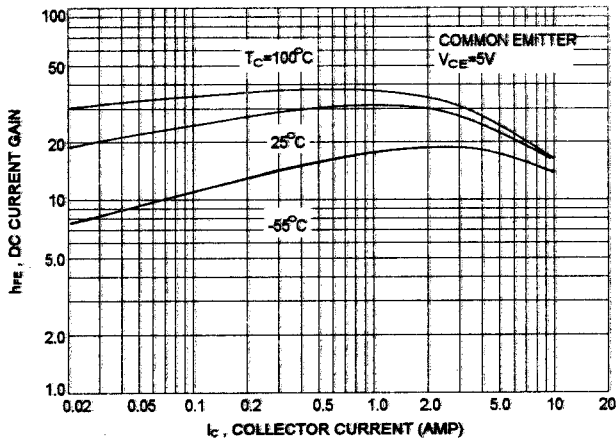
SAFE OPERATING AREA



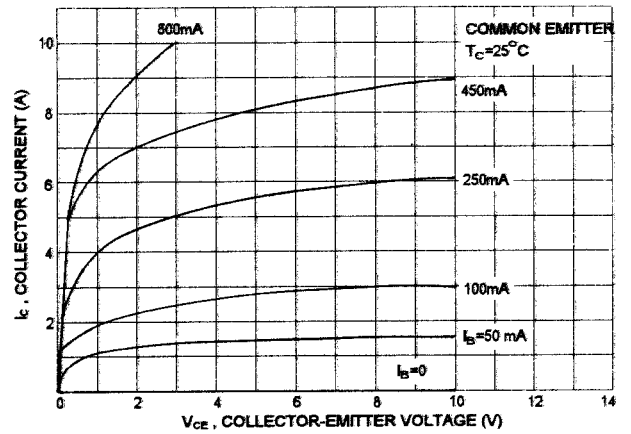
$I_C - V_{BE}$



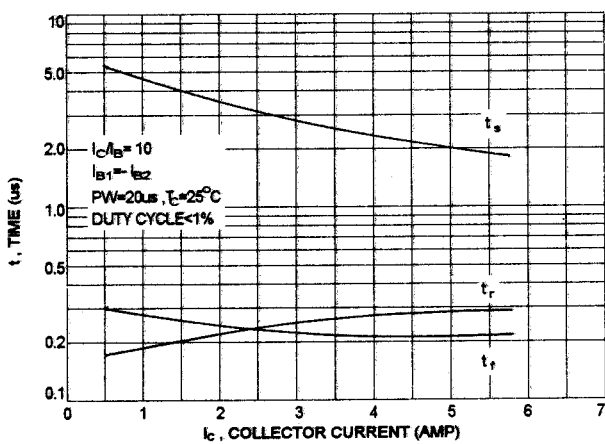
DC CURRENT GAIN



$I_C - V_{CE}$



SWITCHING TIME



"ON" VOLTAGES

